

WHAT IS CLAIMED IS:

*Suba1* 1. A semiconductor device comprising:  
a semiconductor element bonded on a first metallic  
layer;  
5 a wire for electrically connecting an electrode pad of  
the semiconductor element to a second metallic layer; and  
a resin package for sealing said semiconductor element,  
wherein rear surfaces of the first metallic layer and the  
second metallic layer are flush with a bottom of said resin  
10 package.

15 2. A semiconductor device according to claim 1, wherein the  
first metallic layer has a larger area than that of a bottom  
surface of the semiconductor element.

20 3. A semiconductor device according to claim 1, wherein said  
first metallic layer is thicker than said second metallic layer,  
and said first metallic layer has a smaller area than a bottom  
area of the semiconductor element.

25 4. A semiconductor device according to claim 1, wherein said  
second metallic layer is individually exposed from a bottom of  
said resin package.

*Suba2* 5. A method of manufacturing a semiconductor device  
comprising the steps of:  
forming an electrodeposition frame on a flexible flat  
metallic substrate, said electrodeposition frame with first  
25 metallic layers and second metallic layers for external  
extension being patterned;

contiguously mounting a plurality of semiconductor elements each with electrode pads thereon, on said first metallic layers, respectively;

5        wire-bonding the electrode pads to said second metallic layers which are located between said semiconductor elements;

G2        resin-sealing said semiconductor elements mounted on said electrodeposition frame;

removing said metallic substrate to provide a resin sealing body; and

10        cutting said resin sealing body into individual semiconductor devices with the aid of cutting marks formed in the first and second metallic layers.

6.        A method of manufacturing a semiconductor device according to claim 5, further comprising after the step of cutting, the step of:

depositing metallic layers for electrodes to the second metallic layers exposed from a rear surface of said resin sealing body.

20        7.        A method of manufacturing a semiconductor device according to claim 5, wherein

in said step of cutting of said resin sealing body, it is cut along a center line of each of the second metallic layers to provide metallic layers for external extension for adjacent semiconductor elements.

25        8.        A method of manufacturing a semiconductor device

according to claim 5, wherein said electrodeposition frame is resin sealed together with said semiconductor elements using said metallic substrate as a lower die.